

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V_{DRM} and V_{RRM} V	Conditions
DCR490J65*	6500	$T_{vj} = -40^{\circ}\text{C}$ to 125°C , $I_{DRM} = I_{RRM} = 100\text{mA}$, $V_{DRM}, V_{RRM} t_p = 10\text{ms}$, $V_{DSM} \& V_{RSM} =$ $V_{DRM} \& V_{RRM} + 100\text{V}$ respectively
DCR490J60	6000	
DCR490J55	5500	

Lower voltage grades available.
 *6200V @ -40°C , 6500V @ 0°C

KEY PARAMETERS

V_{DRM}	6500V
$I_{T(AV)}$	490A
I_{TSM}	6600A
dV/dt^*	1500V/μs
dI/dt	200A/μs

* Higher dV/dt selections available

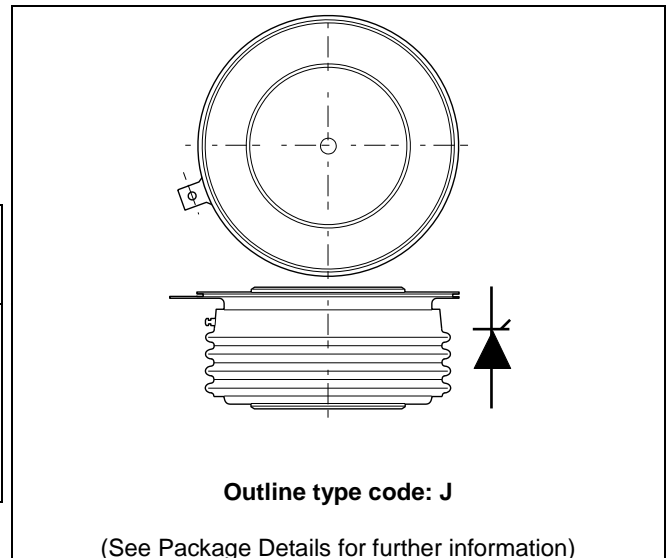


Fig. 1 Package outline

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR490J65

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

CURRENT RATINGS

$T_{case} = 60^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Side Cooled				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	490	A
$I_{T(RMS)}$	RMS value	-	770	A
I_T	Continuous (direct) on-state current	-	730	A

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I_{TSM}	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}\text{C}$	6.6	kA
I^2t	I^2t for fusing	$V_R = 0$	0.22	MA^2s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions	Min.	Max.	Units	
$R_{th(j-c)}$	Thermal resistance – junction to case	Double side cooled	DC	-	0.0379	$^{\circ}\text{C/W}$
		Single side cooled	Anode DC	-	0.0745	$^{\circ}\text{C/W}$
			Cathode DC	-	0.0797	$^{\circ}\text{C/W}$
$R_{th(c-h)}$	Thermal resistance – case to heatsink	Clamping force 11.5kN (with mounting compound)	Double side	-	0.0072	$^{\circ}\text{C/W}$
			Single side	-	.0144	$^{\circ}\text{C/W}$
T_{vj}	Virtual junction temperature	Blocking V_{DRM} / V_{RRM}	-	125	$^{\circ}\text{C}$	
T_{stg}	Storage temperature range		-55	125	$^{\circ}\text{C}$	
F_m	Clamping force		10	13	kN	

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Max.	Units	
I_{RRM}/I_{DRM}	Peak reverse and off-state current	At V_{RRM}/V_{DRM} , $T_{case} = 125^{\circ}C$	-	100	mA	
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V_{DRM} , $T_j = 125^{\circ}C$, gate open	-	1500	V/ μ s	
di/dt	Rate of rise of on-state current	From 67% V_{DRM} to $2x I_{T(AV)}$	Repetitive 50Hz	-	100	A/ μ s
		Gate source 30V, 10 Ω , $t_r < 0.5\mu$ s, $T_j = 125^{\circ}C$	Non-repetitive	-	200	A/ μ s
$V_{T(TO)}$	Threshold voltage – Low level	50A to 400A at $T_{case} = 125^{\circ}C$	-	0.912	V	
	Threshold voltage – High level	400A to 1600A at $T_{case} = 125^{\circ}C$	-	1.108	V	
r_T	On-state slope resistance – Low level	50A to 400A at $T_{case} = 125^{\circ}C$	-	2.157	m Ω	
	On-state slope resistance – High level	400A to 1600A at $T_{case} = 125^{\circ}C$	-	1.647	m Ω	
t_{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10 Ω $t_r = 0.5\mu$ s, $T_j = 25^{\circ}C$	-	3	μ s	
t_q	Turn-off time	$I_T = 500A$, $T_j = 125^{\circ}C$, $V_R = 100V$, $di/dt = 5A/\mu$ s, $dV_{DR}/dt = 20V/\mu$ s linear	550	1100	μ s	
Q_S	Stored charge	$I_T = 500A$, $T_j = 125^{\circ}C$, $di/dt = 5A/\mu$ s,	1800	2600	μ C	
I_{RR}	Reverse recovery current	$I_T = 500A$, $T_j = 125^{\circ}C$, $di/dt = 5A/\mu$ s,	77	90	A	
I_L	Latching current	$T_j = 25^{\circ}C$, $V_D = 5V$	-	3	A	
I_H	Holding current	$T_j = 25^{\circ}C$, $R_{G-K} = \infty$, $I_{TM} = 500A$, $I_T = 5A$	-	300	mA	

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V_{GT}	Gate trigger voltage	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% $V_{DRM}, T_{case} = 125^{\circ}C$	0.4	V
I_{GT}	Gate trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	350	mA
I_{GD}	Gate non-trigger current	At 50% $V_{DRM}, T_{case} = 125^{\circ}C$	15	mA

CURVES

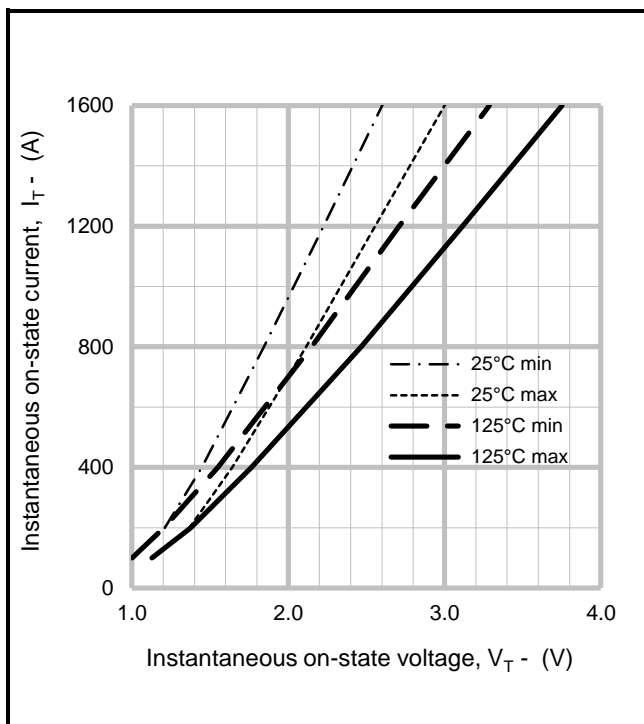


Fig.2 Maximum & minimum on-state characteristics

V_{TM} EQUATION

$$V_{TM} = A + B \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

Where

$$\begin{aligned} A &= 0.542452 \\ B &= 0.065613 \\ C &= 0.001318 \\ D &= 0.015356 \end{aligned}$$

these values are valid for $T_j = 125^{\circ}C$ for I_T 50A to 1600A

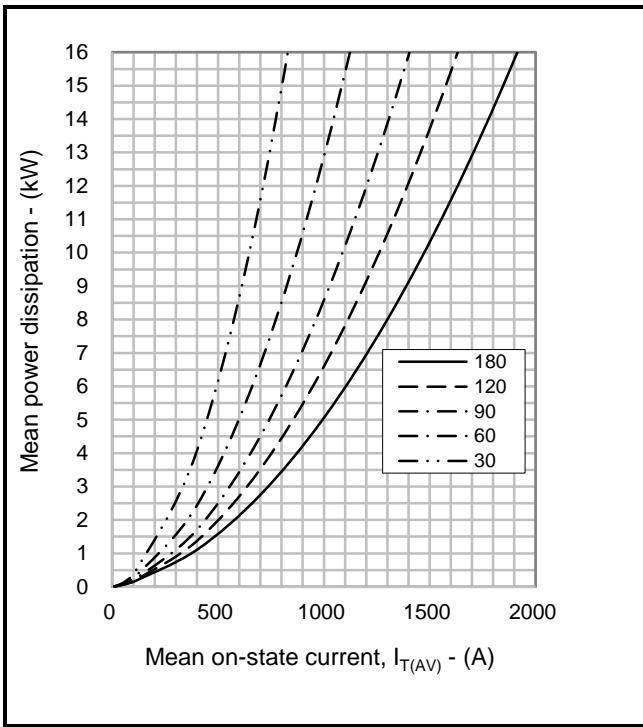


Fig.3 On-state power dissipation – sine wave

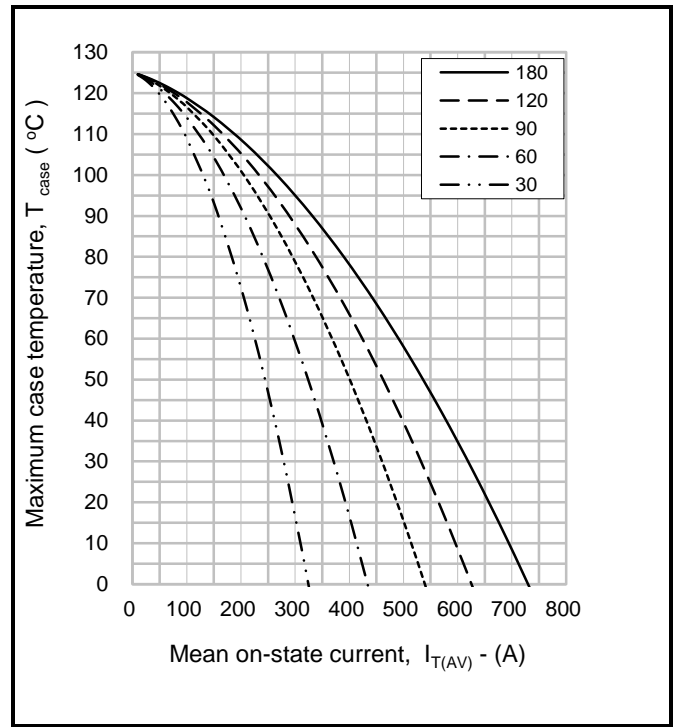


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

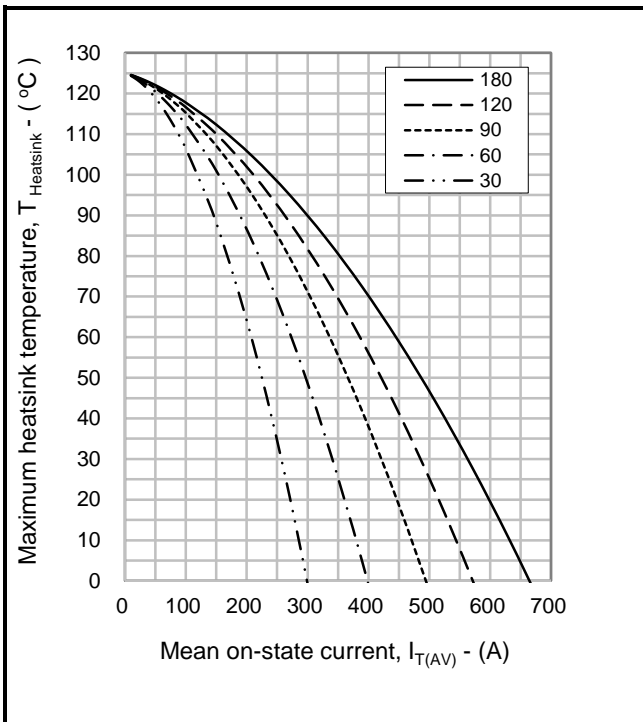


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

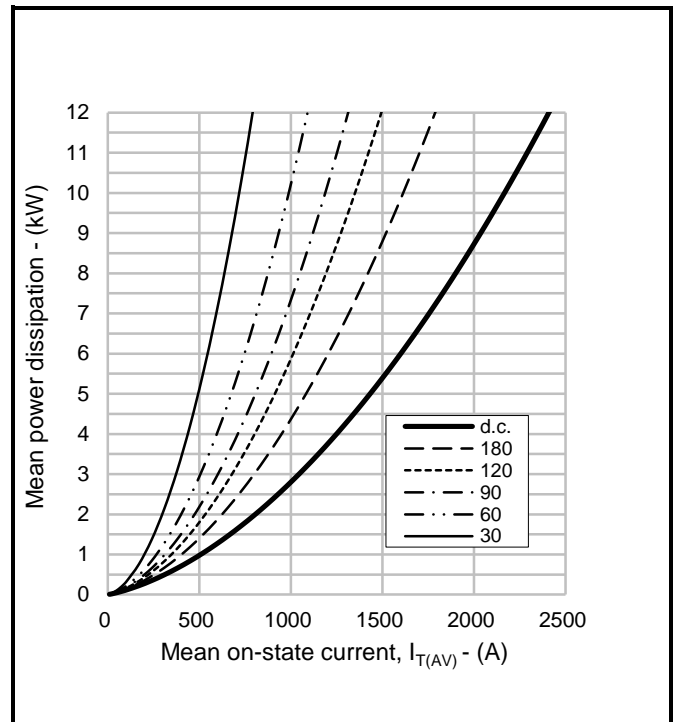


Fig.6 On-state power dissipation – rectangular wave

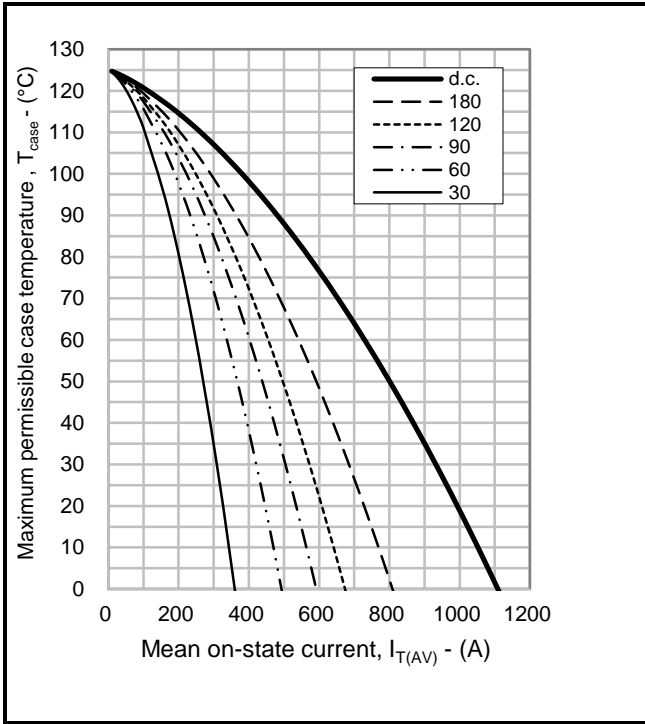


Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave

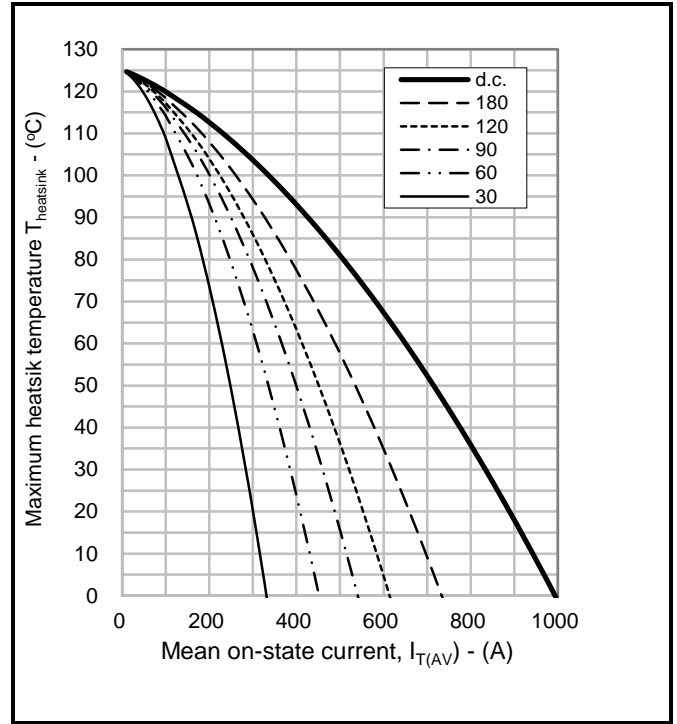


Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave

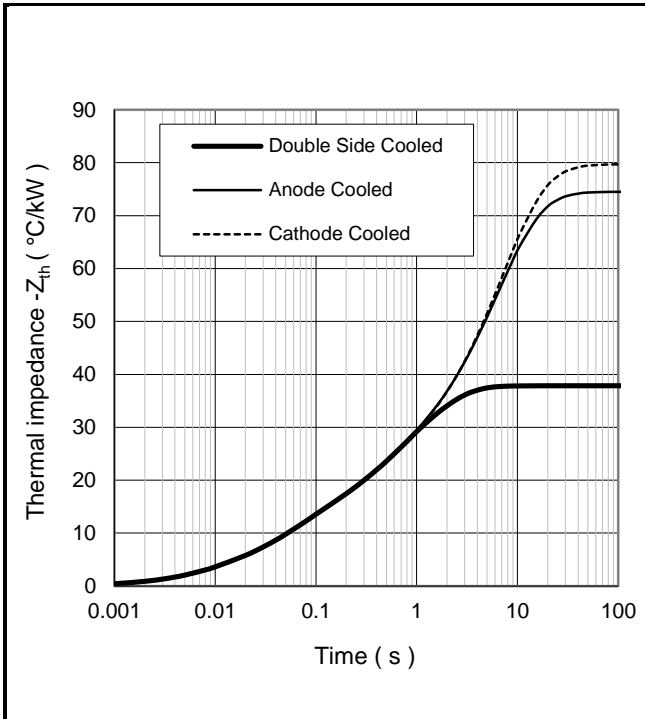


Fig.9 Maximum (limit) transient thermal impedance – junction to case (°C/kW)

		1	2	3	4
Double side cooled	R _i (°C/kW)	2.4256	9.3503	10.6963	15.3758
	T _i (s)	0.0087759	0.053099	0.4497246	1.395
Anode side cooled	R _i (°C/kW)	2.8091	9.5576	11.3564	50.6136
	T _i (s)	0.0097443	0.0591913	0.4759179	6.5548
Cathode side cooled	R _i (°C/kW)	2.9507	9.4031	11.0771	56.0405
	T _i (s)	0.0100391	0.0606056	0.4732916	7.228

$$Z_{th} = \sum_{i=1}^{i=4} [R_i \times (1 - \exp(-T/T_i))]$$

ΔR_{th(j-c)} Conduction

Tables show the increments of thermal resistance R_{th(j-c)} when the device operates at conduction angles other than d.c.

Double side cooling			Anode Side Cooling			Cathode Sided Cooling		
η°	ΔZ _{th} (z)		η°	ΔZ _{th} (z)		η°	ΔZ _{th} (z)	
	sine.	rect.		sine.	rect.		sine.	rect.
180	4.43	3.01	180	4.39	2.99	180	4.37	2.98
120	5.13	4.30	120	5.07	4.26	120	5.05	4.25
90	5.89	5.03	90	5.81	4.97	90	5.79	4.96
60	6.58	5.81	60	6.48	5.74	60	6.45	5.72
30	7.12	6.67	30	7.00	6.57	30	6.97	6.54
15	7.36	7.13	15	7.24	7.01	15	7.20	6.98

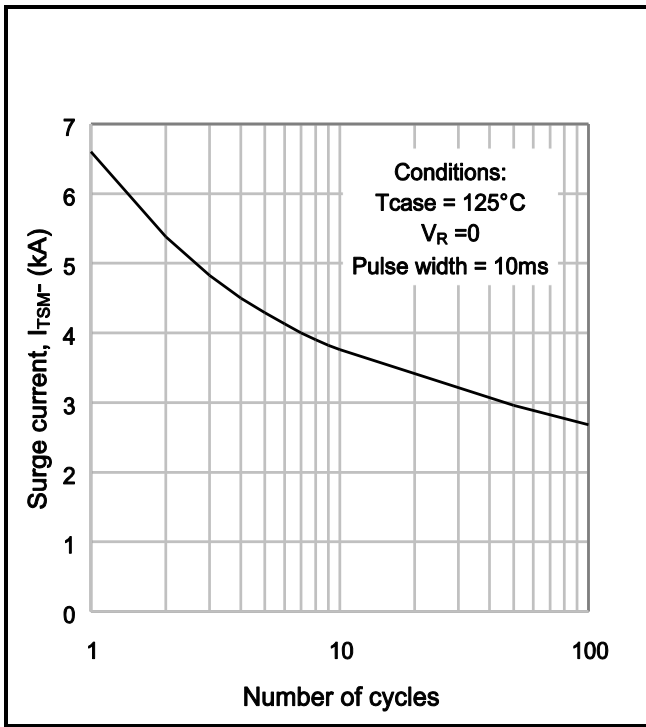


Fig.10 Multi-cycle surge current

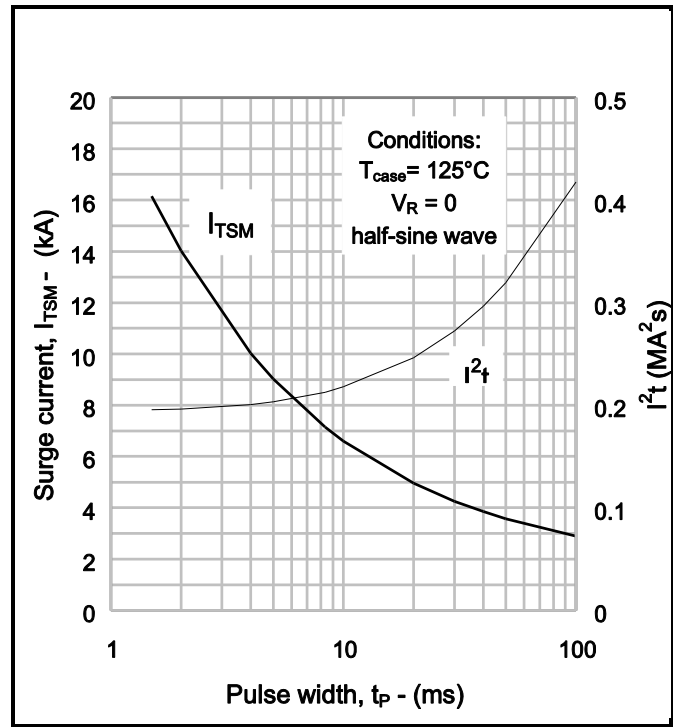


Fig.11 Single-cycle surge current

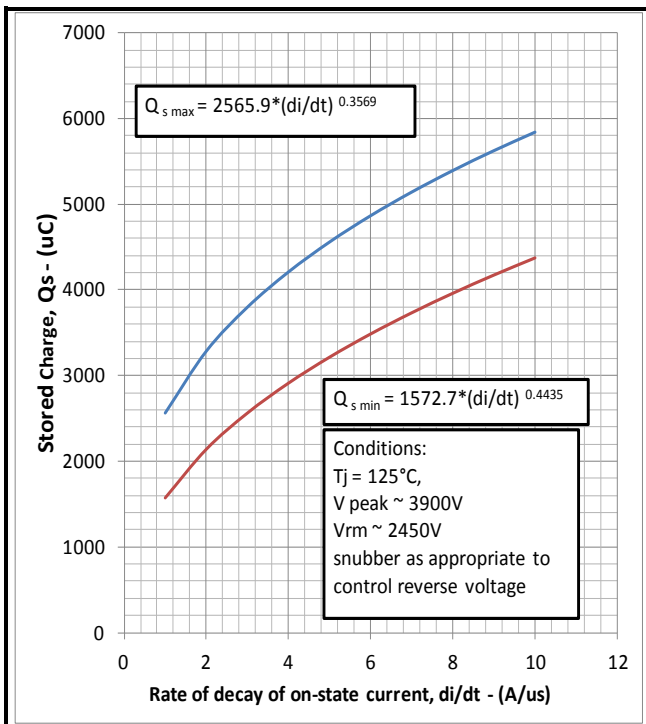


Fig.12 Stored charge vs di/dt

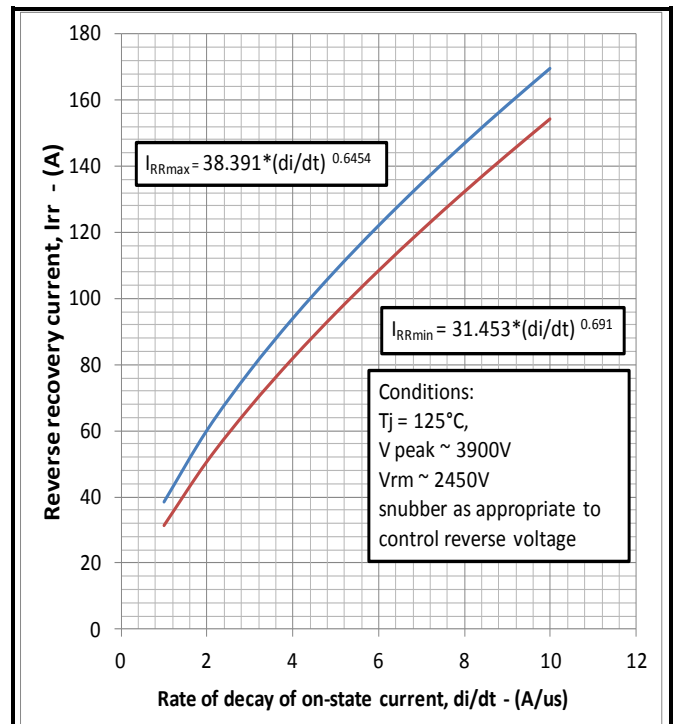


Fig.13 Reverse recovery current vs di/dt

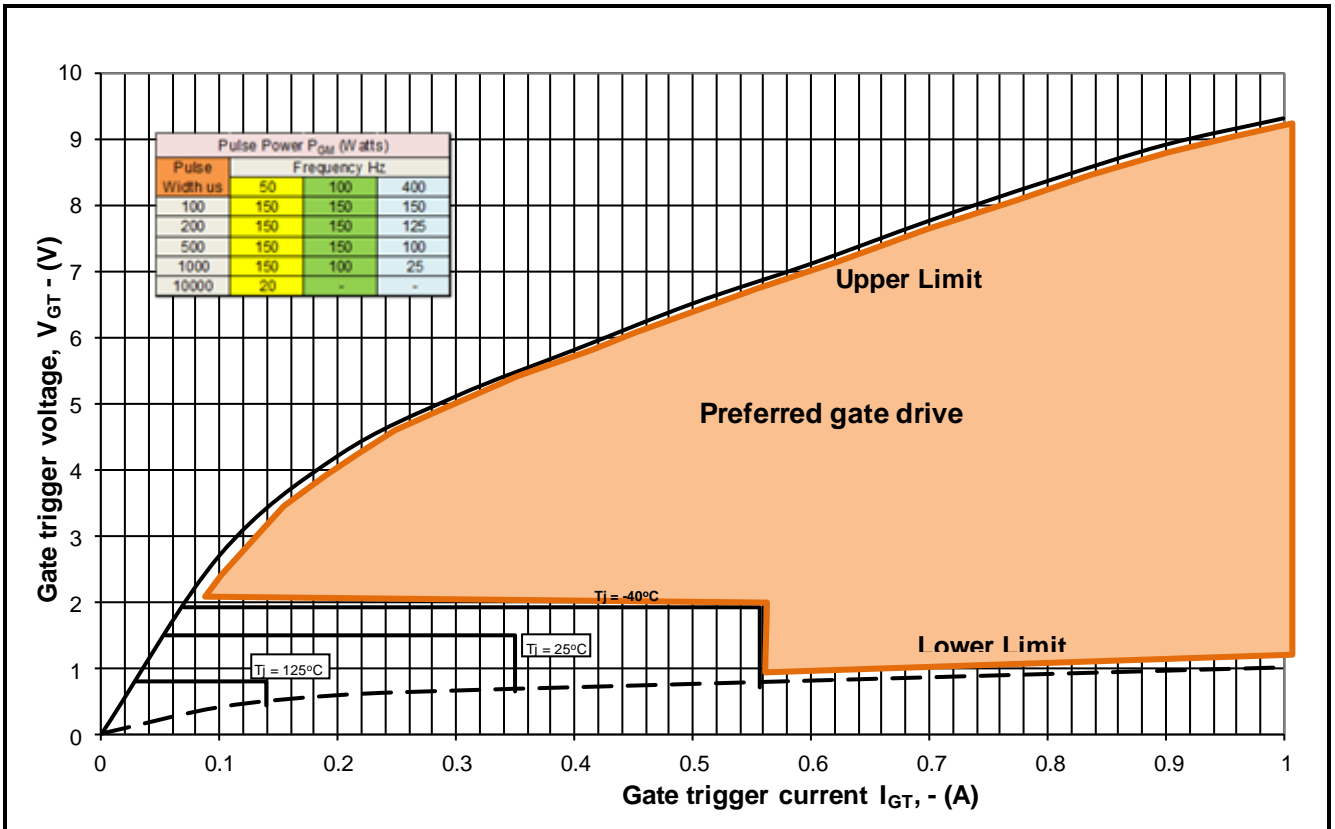


Fig14 Gate Characteristics

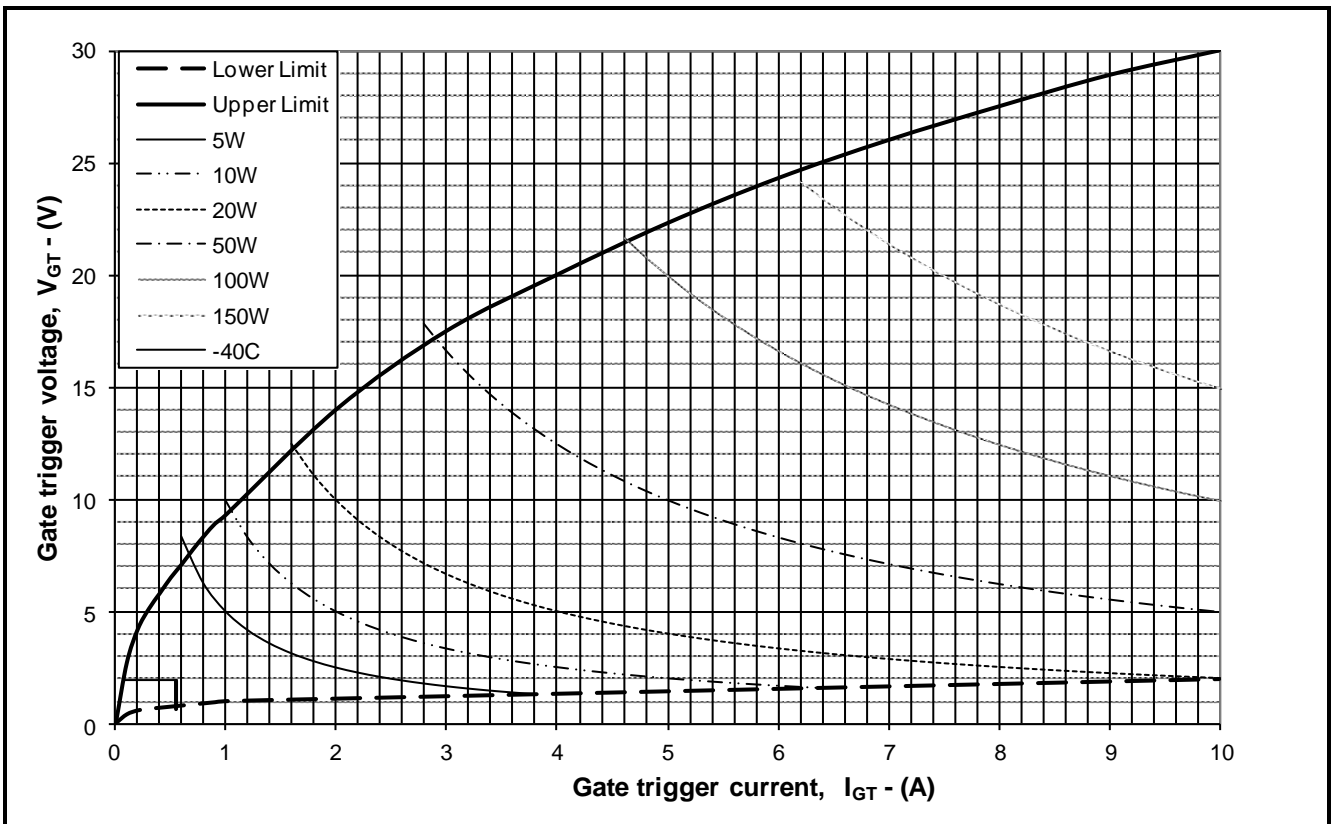


Fig. 15 Gate characteristics

PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

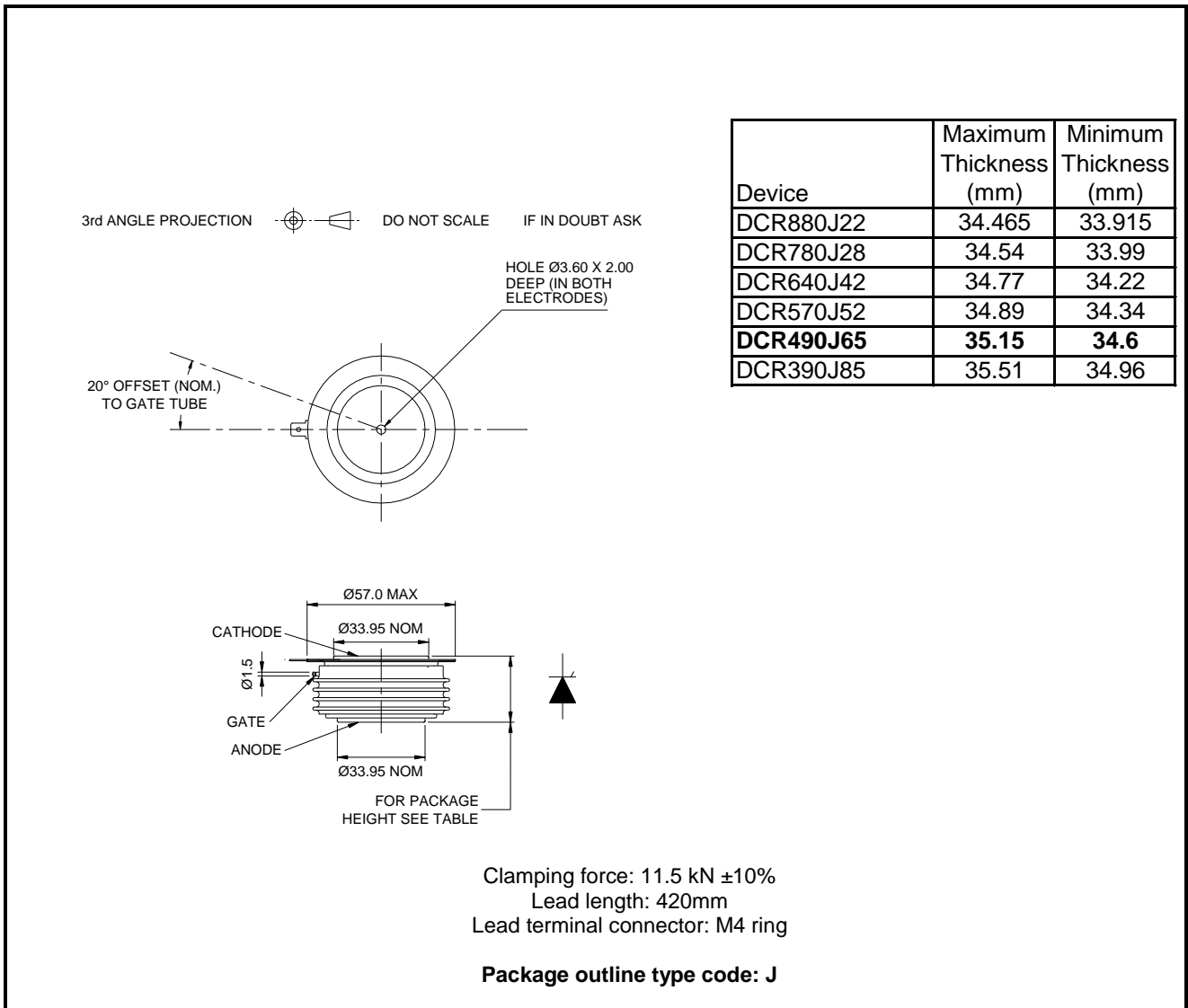


Fig.16 Package outline

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